Description

The NP2302FHR uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and high density cell Design for ultra low on-resistance. This device is suitable for use as a load switch or in PWM applications.

General Features

V_{DS} =20V I_D =3A

$R_{DS(ON)}$(Typ.)=45mΩ @V_{GS}=4.5V

$R_{DS(ON)}$(Typ.)=73mΩ @V_{GS}=2.5V

High power and current handing capability

Lead free product is acquired

Surface mount package

Application

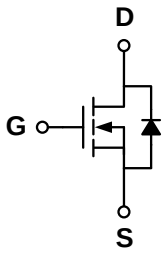
PWM applications

Load switch

Package

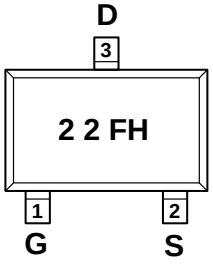
ESOT-23-3L

Schematic diagram



Marking and pin assignment

ESOT-23-3L
(TOP VIEW)



Ordering Information

Part Number	Storage Temperature	Package	Devices Per Reel
NP2302FHR-G	-55°C to +150°C	ESOT-23-3L	3000

Absolute Maximum Ratings (TA=25 unless otherwise noted) -02 18758 5562 169 rere0n0

parameter	symbol	limit	unit
Drain-source voltage	V_{DS}	20	V
Gate-source voltage	V_{GS}	±12	V

Typical Performance Characteristics

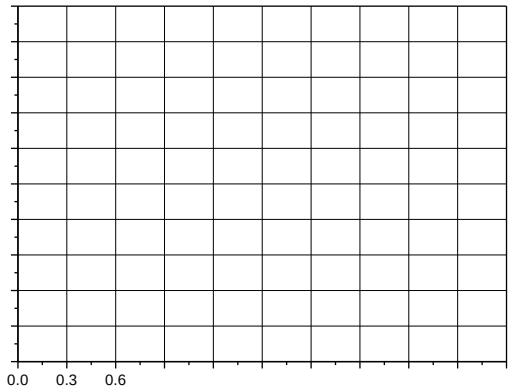


Fig1 Output Characteristics

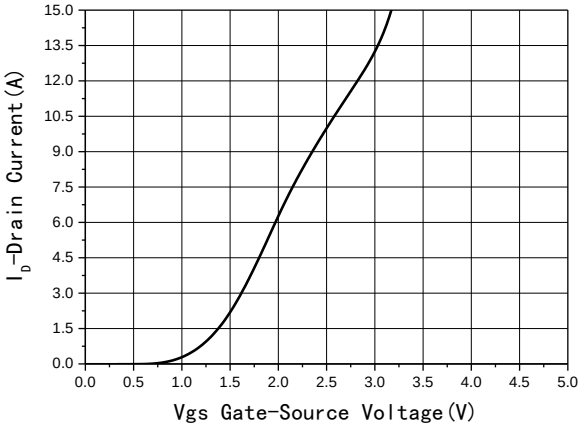


Fig2 Transfer Characteristics

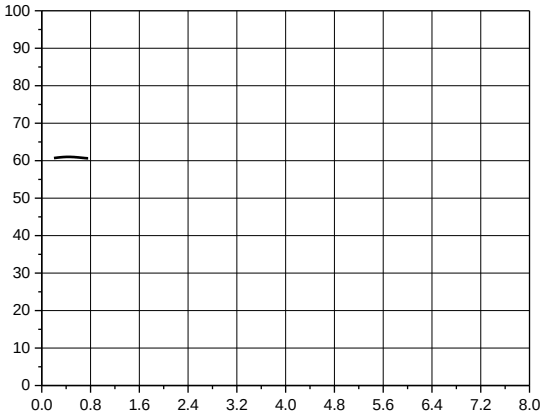


Fig3 Rdson-Drain current

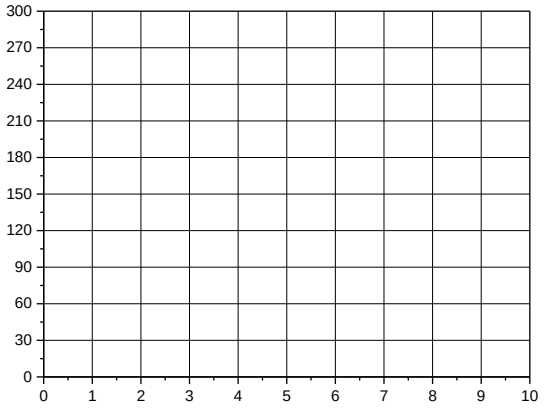


Fig4 Capacitance vs Vds

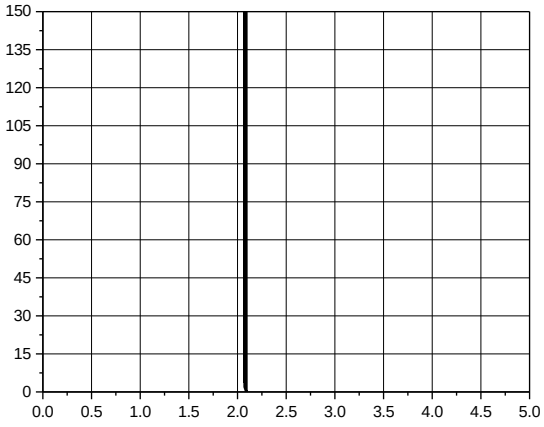


Fig5 Rdson-Gate Drain voltage

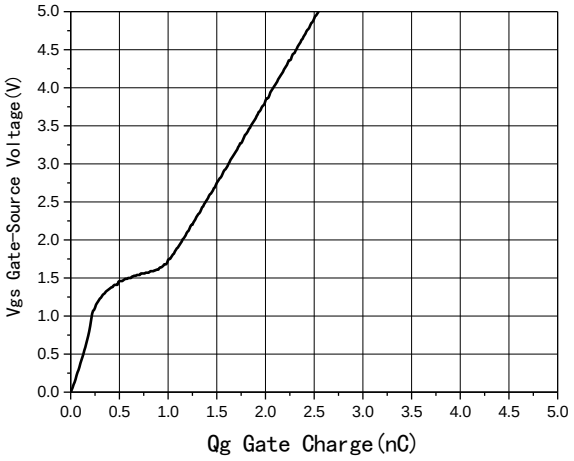


Fig6 Gate Charge

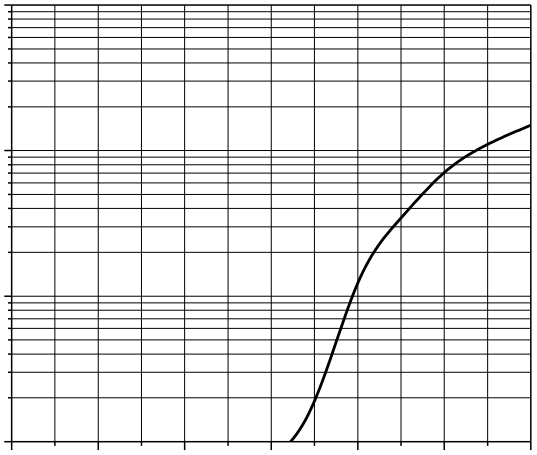


Fig7 Power De-rating

Fig8 Source-Drain Diode Forward

Package Information

ESOT-23-3L

